

| Form PTO 1449<br>(Modified)  |    | U.S. DEPARTMENT OF COMMERCE<br>PATENT AND TRADEMARK OFFICE   |          | ATTY DOCKET NO.<br>239339US2             |                       | SERIAL NO.<br>New Application |  |
|--|----|--|----------|--|-----------------------|-------------------------------|--|
| LIST OF REFERENCES CITED BY APPLICANT  |    |  |          | APPLICANT<br>Yasuyoshi ITOH, et al.      |                       |                               |  |
|  |    |  |          | FILING DATE<br>Herewith                  |                       | GROUP                         |  |
| U.S. PATENT DOCUMENTS  |    |  |          |  |                       |                               |  |
| EXAMINER INITIAL   |    | DOCUMENT NUMBER  | DATE     | NAME                                     | CLASS                 | SUB CLASS                     | FILING DATE IF APPROPRIATE                                       |
|  | AA | 5,768,192  | 06/16/98 | Boaz EITAN                               |                       |                               |  |
|  | AB |  |          |  |                       |                               |  |
|  | AC |  |          |  |                       |                               |  |
|  | AD |  |          |  |                       |                               |  |
|  | AE |  |          |  |                       |                               |  |
|  | AF |  |          |  |                       |                               |  |
|  | AG |  |          |  |                       |                               |  |
|  | AH |  |          |  |                       |                               |  |
|  | AI |  |          |  |                       |                               |  |
|  | AJ |  |          |  |                       |                               |  |
|  | AK |  |          |  |                       |                               |  |
|  | AL |  |          |  |                       |                               |  |
|  | AM |  |          |  |                       |                               |  |
|  | AN |  |          |  |                       |                               |  |
| FOREIGN PATENT DOCUMENTS   |    |  |          |  |                       |                               |  |
|  |    | DOCUMENT NUMBER  | DATE     | COUNTRY                                  | TRANSLATION           |                               |  |
| TT   | AO | 2000-260887  | 09/22/00 | Japan                                    | YES                   | NO                            | X ✓  |
| TT   | AP | 5-75133  | 03/26/93 | Japan (with English extract)             | YES                   | NO                            | X ✓  |
| TT   | AQ | 2002-26149   | 01/25/02 | Japan (with partial English translation) | YES                   | NO                            | X ✓  |
|  | AR |  |          |  |                       |                               |  |
|  | AS |  |          |  |                       |                               |  |
|  | AT |  |          |  |                       |                               |  |
|  | AU |  |          |  |                       |                               |  |
| OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)  |    |  |          |  |                       |                               |  |
| TT   | AV | Ilan BLOOM, et al., "NROM™ – A NEW NON-VOLATILE MEMORY TECHNOLOGY: FROM DEVICE TO PRODUCTS", Microelectronic Engineering 59, 2001, pgs. 213 – 223.   |          |  |                       |                               | ✓  |
| TT   | AW | Toshiyuki TOYOSHIMA, et al., "0.1µm LEVEL CONTACT HOLE PATTERN FORMATION WITH KRF LITHOGRAPHY BY RESOLUTION ENHANCEMENT LITHOGRAPHY ASSISTED BY CHEMICAL SHRINK (RELACS)", IEEE, IEDM, 1998, pgs. 333 – 336.   |          |  |                       |                               | ✓  |
| TT   | AX | J. De BLAUWE, et al., "Si-Dot NON-VOLATILE MEMORY DEVICE", Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, Tokyo, 2001, pgs. 518 – 519.  |          |  |                       |                               | ✓  |
| TT   | AY | Boaz EITAN, et al., "CAN NROM, A 2-BIT, TRAPPING STORAGE NVM CELL, GIVE A REAL CHALLENGE TO FLOATING GATE CELLS?", Presented at the International Conference on Solid State Devices and Materials, Tokyo, 1999, pgs. 1/3 – 3/3.  |          |  |                       |                               | ✓  |
| TT   | AZ | Eli LUSKY, et al., "ELECTRON DISCHARGE MODEL OF LOCALLY-TRAPPED CHARGE IN OXIDE-NITRIDE-OXIDE (ONO) GATES FOR NROM™ NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES", Presented at the Solid State Device and Materials Conference (SSDM 2001), Sep. 2001, Tokyo, Japan, pgs. 1 – 2. |          |  |                       |                               | <input type="checkbox"/> Additional References sheet(s) attached |
| Examiner _____   |    |  |          |  | Date Considered _____ |                               |  |
| *Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. |    |  |          |  |                       |                               |  |